

In the Specification:

Please amend paragraph [0027] on page 8 as follows:

--A problem with the process shown in Figures 1 through 5 is that during the patterning of the bottom electrode layers 120 and 122, an etch by-product 132a or 132b may be deposited on the sidewall of the materials 120 and 122 being patterned, and on one the sidewalls of the dielectric hard mask 128, as shown in Figure 6. For example, if the second conductive material 122 comprises PtMn, PtMn is a noble metal that is etched by physical sputtering. A sputter-etched PtMn layer can easily be re-deposited on the sidewall, in particular when the sidewall is high and vertical.--